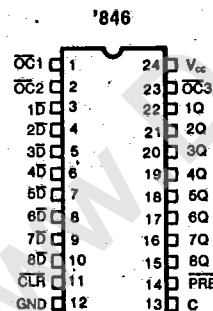
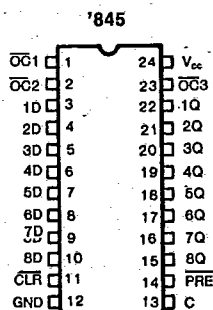


**KS54AHCT 845/846**  
**KS74AHCT**
**8-Bit Bus Interface D-Type**  
**Latches with 3-State Outputs**

T-46-07-05

**Preliminary Specifications**  
**FEATURE**

- 3-state buffer-type outputs drive bus-lines directly
- Bus-structured pinout
- Provides extra bus driving latches necessary for wider address/data paths or buses with parity
- Low power consumption characteristic of CMOS devices
- 3-state outputs with high drive current ( $I_{OL} = 24\text{mA}$  @  $V_{OL} = 0.5\text{V}$ ) for direct bus interface
- Direct interface capability with TTL, NMOS and CMOS devices
- Wide operating voltage range: 4.5V to 5.5V
- Characterized for operation over industrial and military temperature ranges:  
KS74AHCT:  $-40^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$   
KS54AHCT:  $-55^{\circ}\text{C}$  to  $125^{\circ}\text{C}$
- Package options include plastic "small outline" packages, standard plastic and ceramic 300-mil DIPs

**PIN CONFIGURATIONS**

**DESCRIPTION**

These 8-bit latches feature three-state outputs designed specifically for driving highly capacitive or relatively low impedance loads. They are particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

The eight latches are transparent D-type. The '845 has noninverting data(D) inputs. The '846 has inverting D inputs. Since  $\overline{\text{CLR}}$  and  $\overline{\text{PRE}}$  are independent of the clock, taking the  $\overline{\text{CLR}}$  input low will cause the eight Q outputs to go low. Taking the  $\overline{\text{PRE}}$  input low will cause the eight Q outputs to go high. When both  $\overline{\text{PRE}}$  and  $\overline{\text{CLR}}$  are taken low, the outputs will follow the preset condition.

The buffered output control inputs ( $\overline{\text{OC1}}$ ,  $\overline{\text{OC2}}$ , and  $\overline{\text{OC3}}$ ) can be used to place the eight outputs in either a normal logic state (high or low levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive the bus lines in a bus-organized system without need for interface or pull-up components. The output controls do not affect the internal operation of the latches. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

These devices provide speeds and drive capability equivalent to their ALSTTL counterparts and yet maintain CMOS power levels. The input and output voltage levels allow direct interface with TTL, NMOS and CMOS devices without any external components.

All inputs and outputs are protected from damage due to static discharge by internal diode clamps to  $V_{CC}$  and ground.

**KS54AHCT 845/846**  
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**Latches with 3-State Outputs**

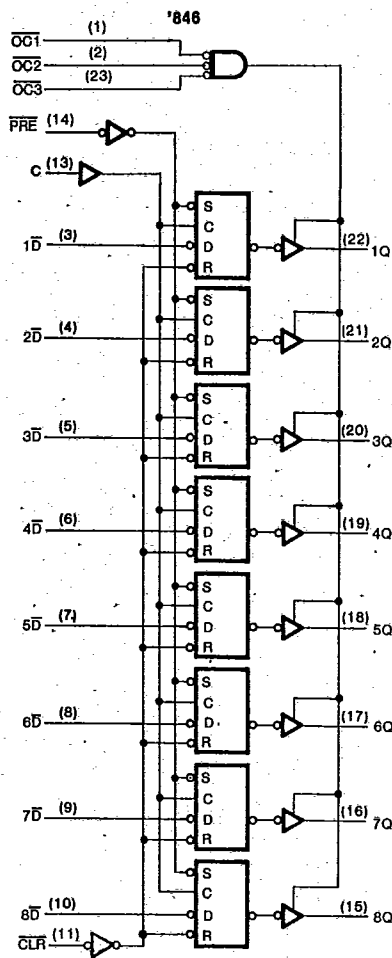
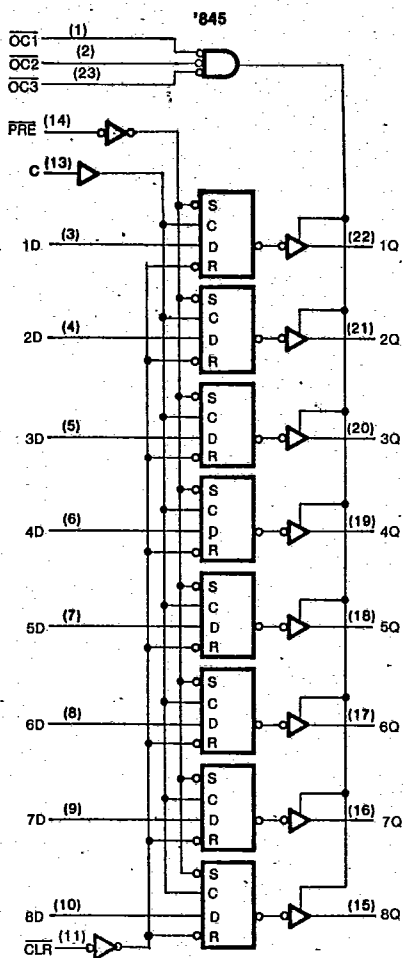
T-46-07-05

**FUNCTION TABLE**

'845							
INPUTS							OUTPUT
PRE	CLR	OC1	OC2	OC3	C	D	Q
L	H	L	L	L	X	X	H
H	L	L	L	L	X	X	L
L	L	L	L	L	X	X	H
H	H	L	L	L	H	L	L
H	H	L	L	L	H	H	H
H	H	L	L	L	L	X	Q <sub>0</sub>
X	X	X	X	H	X	X	Z
X	X	X	H	X	X	X	Z
X	X	H	X	X	X	X	Z

'846							
INPUTS							OUTPUT
PRE	CLR	OC1	OC2	OC3	C	D	Q
L	H	L	L	L	X	X	H
H	L	L	L	L	X	X	L
L	L	L	L	L	X	X	H
H	H	L	L	L	H	L	H
H	H	L	L	L	H	H	L
H	H	L	L	L	L	X	Q <sub>0</sub>
X	X	X	X	H	X	X	Z
X	X	X	H	X	X	X	Z
X	X	H	X	X	X	X	Z

**LOGIC DIAGRAMS**



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**KS54AHCT 845/846**  
**KS74AHCT**

**8-Bit Bus Interface D-Type**  
**Latches with 3-State Outputs**

T-46-07-05

**Absolute Maximum Ratings\***

Supply Voltage Range  $V_{CC}$  . . . . . -0.5V to +7V  
 DC Input Diode Current,  $I_{IK}$   
 ( $V_I < -0.5V$  or  $V_I > V_{CC} + 0.5V$ ) . . . . .  $\pm 20$  mA  
 DC Output Diode Current,  $I_{OK}$   
 ( $V_O < -0.5V$  or  $V_O > V_{CC} + 0.5V$ ) . . . . .  $\pm 20$  mA  
 Continuous Output Current Per Pin,  $I_O$   
 ( $-0.5V < V_O < V_{CC} + 0.5V$ ) . . . . .  $\pm 70$  mA  
 Continuous Current Through  
 $V_{CC}$  or GND pins . . . . .  $\pm 250$  mA  
 Storage Temperature Range,  $T_{stg}$  . . . . . -65°C to +150°C  
 Power Dissipation Per Package,  $P_d$ † . . . . . 500 mW

\* Absolute Maximum Ratings are those values beyond which permanent damage to the device may occur. These are stress ratings only and functional operation of the device at or beyond them is not implied. Long exposure to these conditions may affect device reliability.

† Power Dissipation temperature derating:  
 Plastic Package (N): -12mW/°C from 65°C to 85°C  
 Ceramic Package (J): -12mW/°C from 100°C to 125°C

**Recommended Operating Conditions**

Supply Voltage,  $V_{CC}$  . . . . . 4.5V to 5.5V  
 DC Input & Output Voltages\*,  $V_{IN}, V_{OUT}$  . . . . . 0V to  $V_{CC}$   
 Operating Temperature  
 Range KS74AHCT: -40°C to +85°C  
 KS54AHCT: -55°C to +125°C  
 Input Rise & Fall Times,  $t_r, t_f$  . . . . . Max 500 ns

\* Unused inputs must always be tied to an appropriate logic voltage level (either  $V_{CC}$  or GND)

**DC ELECTRICAL CHARACTERISTICS** ( $V_{CC}=5V \pm 10\%$  Unless Otherwise Specified)

Characteristic	Symbol	Test Conditions	$T_a = 25^\circ C$			Unit	
			Typ	KS74AHCT $T_a = -40^\circ C$ to $+85^\circ C$	KS54AHCT $T_a = -55^\circ C$ to $+125^\circ C$		
Minimum High-Level Input Voltage	$V_{IH}$			2.0	2.0	2.0	V
Maximum Low-Level Input Voltage	$V_{IL}$			0.8	0.8	0.8	V
Minimum High-Level Output Voltage	$V_{OH}$	$V_{IN} = V_{IH}$ or $V_{IL}$ $I_O = -20\mu A$ $I_O = -4mA$	$V_{CC}$ 4.2	$V_{CC} - 0.1$ 3.98	$V_{CC} - 0.1$ 3.84	$V_{CC} - 0.1$ 3.7	V
Maximum Low-Level Output Voltage	$V_{OL}$	$V_{IN} = V_{IH}$ or $V_{IL}$ $I_O = 20\mu A$ $I_O = 4mA$ $I_O = 8mA$	0	0.1 0.26 0.39	0.1 0.33 0.5	0.1 0.4	V
Maximum Input Current	$I_{IN}$	$V_{IN} = V_{CC}$ or GND		$\pm 0.1$	$\pm 1.0$	$\pm 1.0$	$\mu A$
Maximum Quiescent Supply Current	$I_{CC}$	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0\mu A$		8.0	80.0	160.0	$\mu A$
Additional Worst Case Supply Current	$\Delta I_{CC}$	per input in $V_I = 2.4V$ other inputs: at $V_{CC}$ or GND $I_{OUT} = 0\mu A$		2.7	2.9	3.0	mA

KS54AHCT  
KS74AHCT **845/846****8-Bit Bus Interface D-Type  
Latches with 3-State Outputs**

T-46-07-05

**AC ELECTRICAL CHARACTERISTICS** (Input  $t_r, t_f \leq 2$  ns), AHCT845

Characteristic	Symbol	Conditions†	$T_a = 25^\circ\text{C}$ $V_{CC} = 5.0\text{V}$	KS74AHCT $T_a = -40^\circ\text{C to } +85^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$		KS54AHCT $T_a = -55^\circ\text{C to } +125^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$		Unit
			Typ	Min	Max	Min	Max	
Propagation Delay Clk to Q	$t_{PLH}$		13†		22		26	ns
	$t_{PHL}$		13		22		26	
Propagation Delay D to Q	$t_{PLH}$		8		15		20	ns
	$t_{PHL}$		8		15		20	
Propagation Delay CLR to Q	$t_{PLH}$		16		26		31	ns
	$t_{PHL}$		16		26		31	
Propagation Delay PRE to Q	$t_{PLH}$		16		26		31	ns
	$t_{PHL}$		16		26		31	
Propagation Delay OC to Q	$t_{PZH}$		12		20		24	ns
	$t_{PZL}$		12		20		24	
Propagation Delay OC to Q	$t_{PHZ}$		12		20		24	ns
	$t_{PLZ}$		12		20		24	
Input Capacitance	$C_{IN}$		5					pF
Power dissipation Capacitance*	$C_{PD}$							pF

\*  $C_{PD}$  determines the no-load dynamic power dissipation:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ .

† For AC switching test circuits and timing waveforms see section 2.

**AC ELECTRICAL CHARACTERISTICS** (Input  $t_r, t_f \leq 2$  ns), AHCT846

Characteristic	Symbol	Conditions†	$T_a = 25^\circ\text{C}$ $V_{CC} = 5.0\text{V}$	KS74AHCT $T_a = -40^\circ\text{C to } +85^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$		KS54AHCT $T_a = -55^\circ\text{C to } +125^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$		Unit
			Typ	Min	Max	Min	Max	
Propagation Delay Clk to Q	$t_{PLH}$		14		24		32	ns
	$t_{PHL}$		14		24		32	
Propagation Delay D to Q	$t_{PLH}$		10		17		22	ns
	$t_{PHL}$		10		17		22	
Propagation Delay CLR to Q	$t_{PLH}$		13		22		26	ns
	$t_{PHL}$		13		22		26	
Propagation Delay PRE to Q	$t_{PLH}$		13		22		26	ns
	$t_{PHL}$		13		22		26	
Propagation Delay OC to Q	$t_{PZH}$		12		20		24	ns
	$t_{PZL}$		12		20		24	
Propagation Delay OC to Q	$t_{PHZ}$		12		20		24	ns
	$t_{PLZ}$		12		20		24	
Input Capacitance	$C_{IN}$		5					pF
Power dissipation Capacitance*	$C_{PD}$							pF

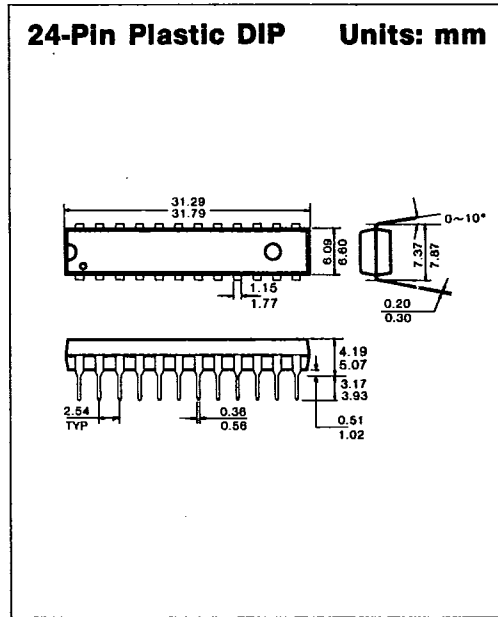
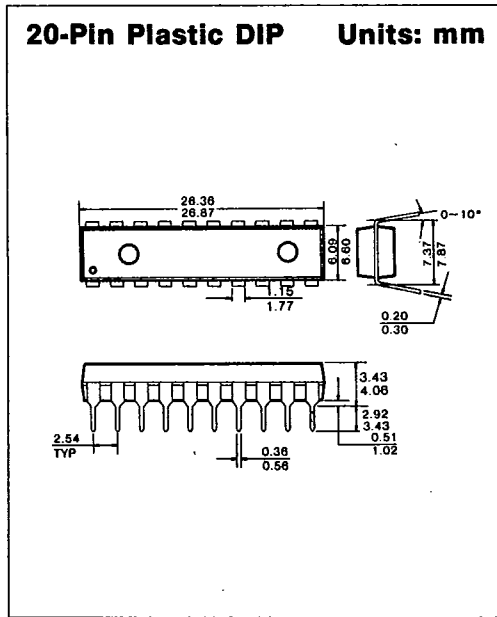
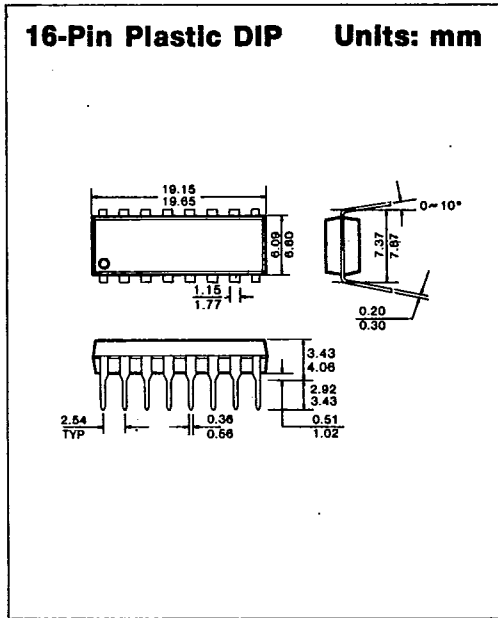
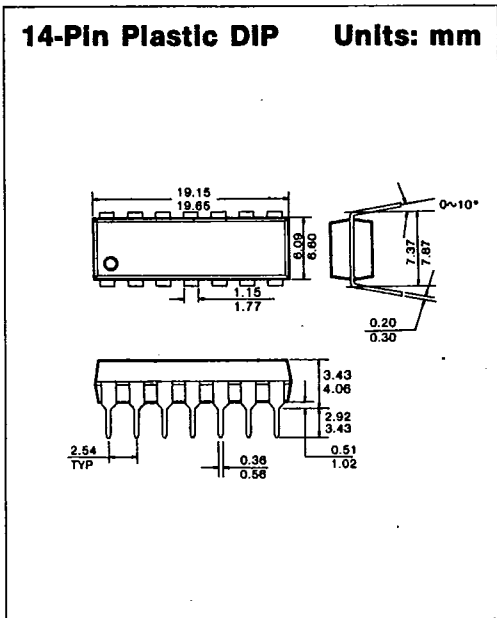
\*  $C_{PD}$  determines the no-load dynamic power dissipation:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ .

† For AC switching test circuits and timing waveforms see section 2.

**PACKAGE DIMENSIONS**

T-90-20

**1. PLASTIC PACKAGES**



7



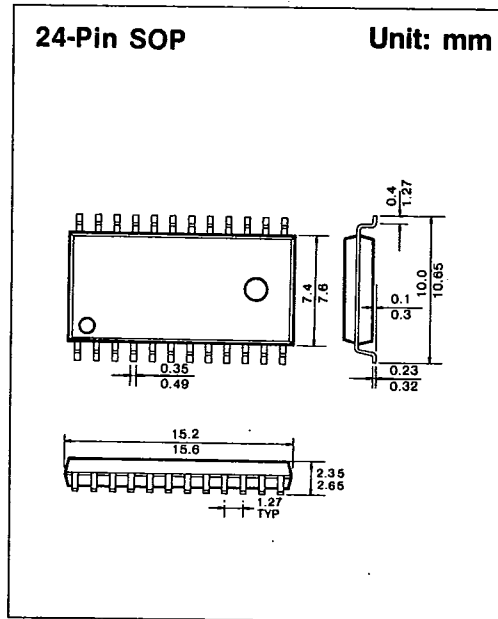
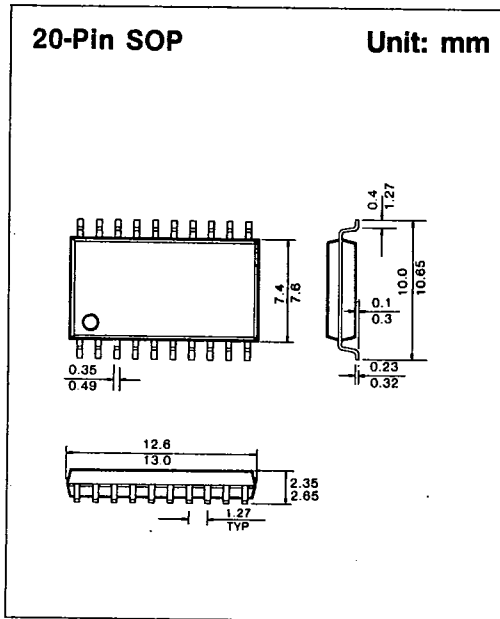
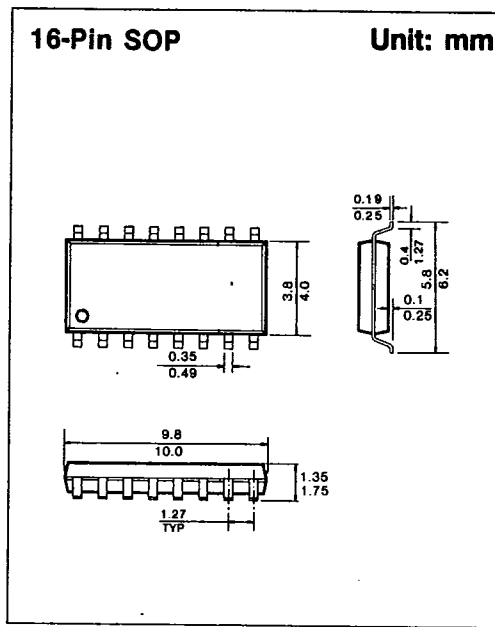
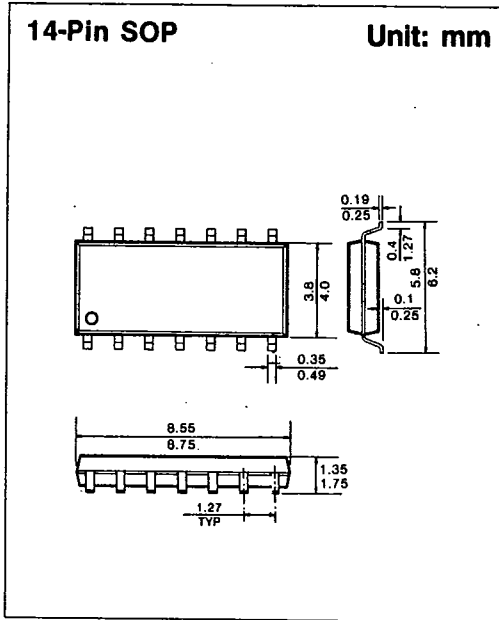
SAMSUNG SEMICONDUCTOR

1675

A-04

**PACKAGE DIMENSIONS**

T-90-20

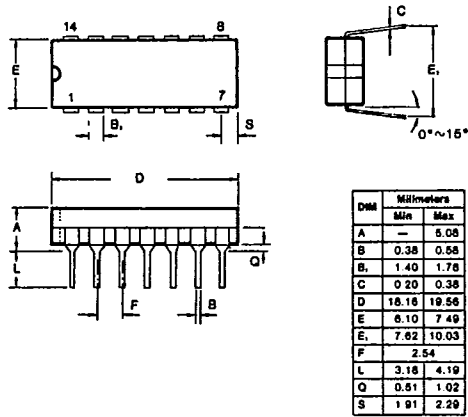


**PACKAGE DIMENSIONS**

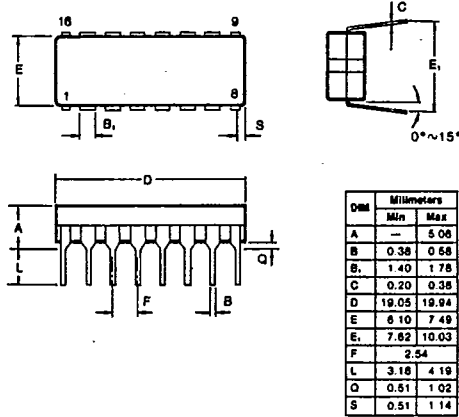
T-90-20

**2. CERAMIC PACKAGES**

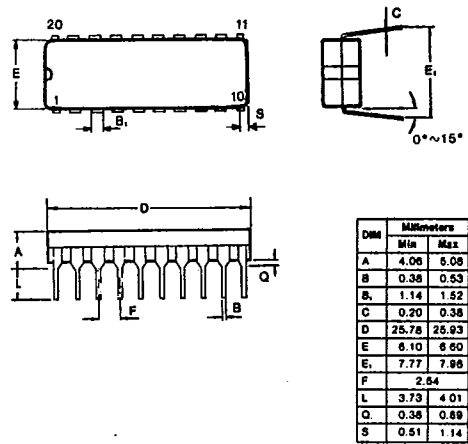
**14-Pin Ceramic DIP Units: mm**



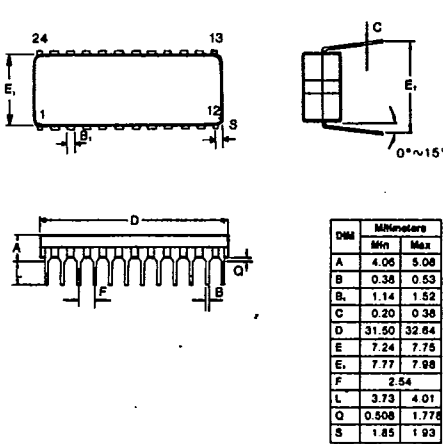
**16-Pin Ceramic DIP Units: mm**



**20-Pin Ceramic DIP Units: mm**



**24-Pin Ceramic DIP Units: mm**



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